



## IGBT module

## SK35GD12T4ETp

## Features\*

- One screw mounting module
- Solder free mounting with Press-Fit terminals
- Fully compatible with other SEMITOP® Press-Fit types
- Trench4 IGBT technology
- CAL4F technology FWD
- Integrated NTC temperature sensor
- UL recognized, file no. E 63 532

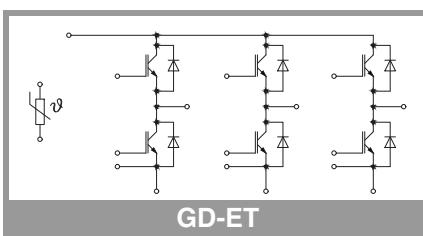
## Typical Applications

- Motor Drives
- Servo Drives
- Air Conditioning
- Auxiliary Inverters
- UPS

Absolute Maximum Ratings		Values	Unit	
Symbol	Conditions			
<b>IGBT 1</b>				
$V_{CES}$	$T_j = 25^\circ\text{C}$	1200	V	
$I_c$	$T_j = 150^\circ\text{C}$	38	A	
	$T_s = 25^\circ\text{C}$	29	A	
$I_c$	$T_j = 175^\circ\text{C}$	43	A	
	$T_s = 70^\circ\text{C}$	35	A	
$I_{Cnom}$		35	A	
$I_{CRM}$	$I_{CRM} = 3 \times I_{Cnom}$	105	A	
$V_{GES}$		-20 ... 20	V	
$t_{psc}$	$V_{CC} = 800\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 1200\text{ V}$	$T_j = 150^\circ\text{C}$	10	$\mu\text{s}$
$T_j$			-40 ... 175	$^\circ\text{C}$

Absolute Maximum Ratings		Values	Unit
Symbol	Conditions		
<b>Diode 1</b>			
$V_{RRM}$	$T_j = 25^\circ\text{C}$	1200	V
$I_F$	$T_j = 150^\circ\text{C}$	34	A
	$T_s = 25^\circ\text{C}$	25	A
$I_F$	$T_j = 175^\circ\text{C}$	38	A
	$T_s = 70^\circ\text{C}$	30	A
$I_{Fnom}$		35	A
$I_{FRM}$	$I_{FRM} = 2 \times I_{Fnom}$	70	A
$I_{FSM}$	$10\text{ ms, sin }180^\circ, T_j = 150^\circ\text{C}$	170	A
$T_j$		-40 ... 175	$^\circ\text{C}$

Absolute Maximum Ratings		Values	Unit
Symbol	Conditions		
<b>Module</b>			
$I_{t(RMS)}$	$\Delta T_{\text{terminal}} \text{ at PCB joint} = 30\text{ K, per pin}$	35	A
$T_{stg}$		-40 ... 125	$^\circ\text{C}$
$V_{isol}$	AC, sinusoidal, $t = 1\text{ min}$	2500	V





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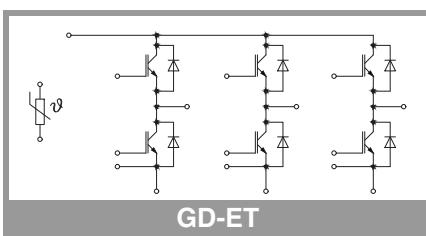
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Characteristics		Conditions	min.	typ.	max.	Unit
Symbol						
<b>IGBT 1</b>						
$V_{CE(sat)}$	$I_C = 35 \text{ A}$	$T_j = 25^\circ\text{C}$		1.85	2.10	V
	$V_{GE} = 15 \text{ V}$ chiplevel	$T_j = 150^\circ\text{C}$		2.25	2.45	V
$V_{CE0}$	chiplevel	$T_j = 25^\circ\text{C}$		0.80	0.90	V
		$T_j = 150^\circ\text{C}$		0.70	0.80	V
$r_{CE}$	$V_{GE} = 15 \text{ V}$ chiplevel	$T_j = 25^\circ\text{C}$		30	34	$\text{m}\Omega$
		$T_j = 150^\circ\text{C}$		44	47	$\text{m}\Omega$
$V_{GE(\text{th})}$	$V_{GE} = V_{CE}, I_C = 1.2 \text{ mA}$		5	5.8	6.5	V
$I_{CES}$	$V_{GE} = 0 \text{ V}$	$T_j = 25^\circ\text{C}$		-	1	$\text{mA}$
	$V_{CE} = 1200 \text{ V}$			-		$\text{mA}$
$C_{ies}$		$f = 1 \text{ MHz}$		1.95		$\text{nF}$
$C_{oes}$	$V_{CE} = 25 \text{ V}$	$f = 1 \text{ MHz}$		0.155		$\text{nF}$
$C_{res}$	$V_{GE} = 0 \text{ V}$	$f = 1 \text{ MHz}$		0.115		$\text{nF}$
$Q_G$	$V_{GE} = -7 \text{ V} \dots +15 \text{ V}$			190		$\text{nC}$
$R_{Gint}$	$T_j = 25^\circ\text{C}$			0		$\Omega$
$t_{d(on)}$	$V_{CC} = 600 \text{ V}$	$T_j = 150^\circ\text{C}$		28		ns
$t_r$	$I_C = 35 \text{ A}$	$T_j = 150^\circ\text{C}$		25		ns
$E_{on}$	$V_{GE \text{ neg}} = -7 \text{ V}$	$T_j = 150^\circ\text{C}$		3.2		$\text{mJ}$
$t_{d(off)}$	$V_{GE \text{ pos}} = 15 \text{ V}$	$T_j = 150^\circ\text{C}$		303		ns
$t_f$	$R_{G \text{ on}} = 22 \Omega$	$T_j = 150^\circ\text{C}$		70		ns
	$R_{G \text{ off}} = 22 \Omega$	$T_j = 150^\circ\text{C}$				
	$di/dt_{on} = 2500 \text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$				
	$di/dt_{off} = 1500 \text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$				
$E_{off}$	$dv/dt = 2900 \text{ V}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		3.3		$\text{mJ}$
$R_{th(j-s)}$	per IGBT, $\lambda_{\text{paste}}=0.8 \text{ W}/(\text{mK})$			1.21		K/W

Characteristics		Conditions	min.	typ.	max.	Unit
Symbol						
<b>Diode 1</b>						
$V_F$	$I_F = 35 \text{ A}$	$T_j = 25^\circ\text{C}$		2.30	2.62	V
	chiplevel	$T_j = 150^\circ\text{C}$		2.29	2.62	V
$V_{F0}$	chiplevel	$T_j = 25^\circ\text{C}$		1.30	1.50	V
		$T_j = 150^\circ\text{C}$		0.90	1.10	V
$r_F$	chiplevel	$T_j = 25^\circ\text{C}$		29	32	$\text{m}\Omega$
		$T_j = 150^\circ\text{C}$		40	43	$\text{m}\Omega$
$I_{RRM}$	$I_F = 35 \text{ A}$	$T_j = 150^\circ\text{C}$		30		A
$Q_{rr}$	$di/dt_{off} = 2500 \text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		2		$\mu\text{C}$
$E_{rr}$	$V_{GE} = -7 \text{ V}$	$T_j = 150^\circ\text{C}$		1.4		$\text{mJ}$
$R_{th(j-s)}$	per Diode, $\lambda_{\text{paste}}=0.8 \text{ W}/(\text{mK})$			1.55		K/W



# SK35GD12T4ETp

**SEMITOP® 3 Press-Fit**

## IGBT module

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#### Features\*

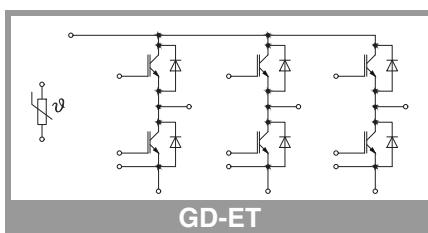
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Characteristics		Symbol	Conditions	min.	typ.	max.	Unit
<b>Module</b>							
M <sub>s</sub>	to heatsink			2.25		2.5	Nm
w	weight				30		g

Characteristics		Symbol	Conditions	min.	typ.	max.	Unit
<b>Temperature Sensor</b>							
R <sub>100</sub>	T <sub>r</sub> = 100 °C			493 ± 5%			Ω
B <sub>100/125</sub>	R <sub>(T)</sub> =R <sub>100</sub> exp[B <sub>100/125</sub> (1/T-1/T <sub>100</sub> )]; T[K];			3550		±2%	K



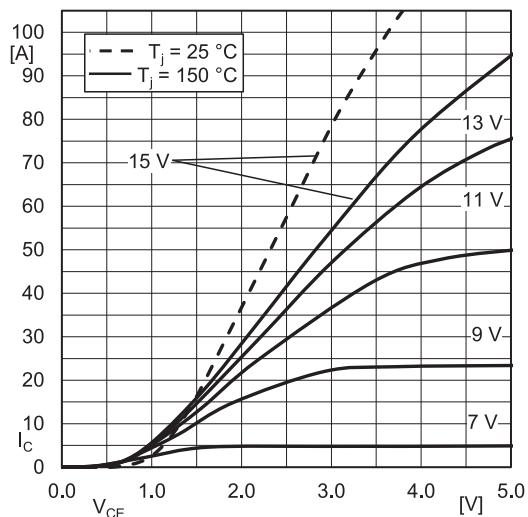


Fig. 1: Typ. IGBT1 output characteristic, incl.  $R_{CC} + EE'$

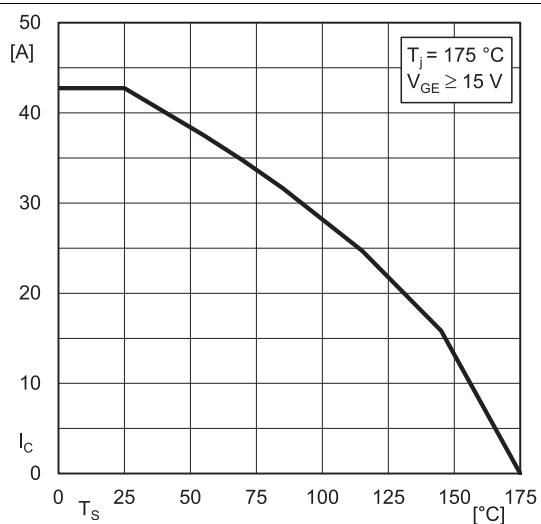


Fig. 2: Typ. rated current vs. temperature  $I_C = f(T_S)$

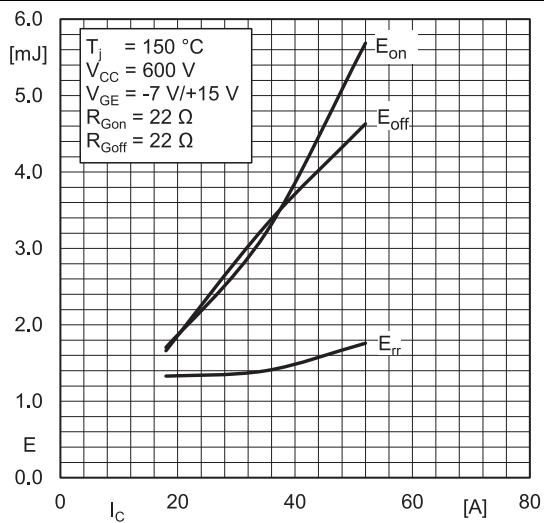


Fig. 3: Typ. turn-on /-off energy =  $f(I_C)$

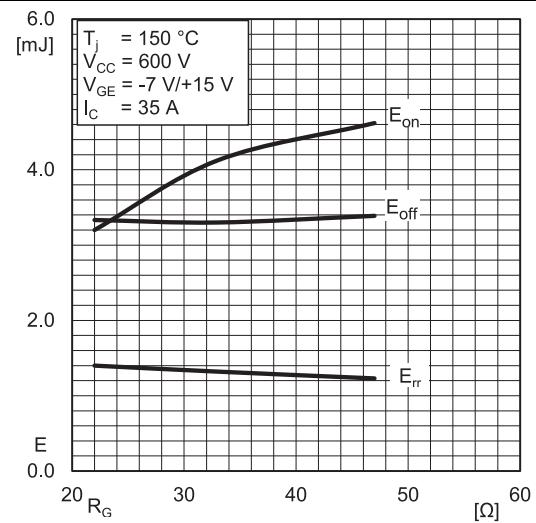


Fig. 4: Typ. turn-on /-off energy =  $f(R_G)$

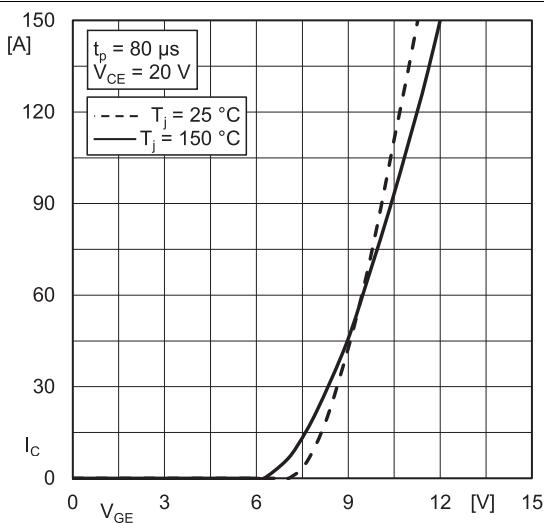


Fig. 5: Typ. IGBT1 transfer characteristic

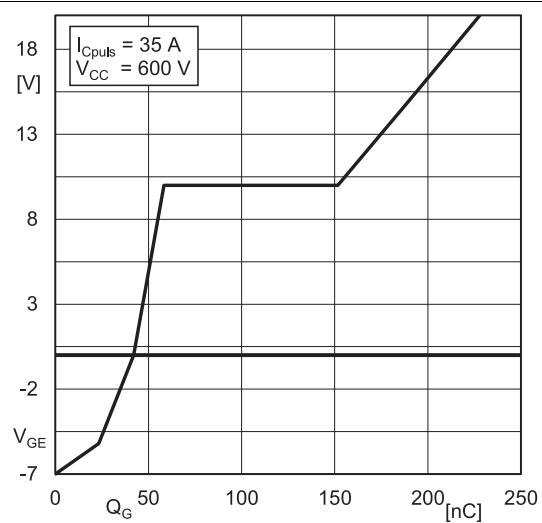


Fig. 6: Typ. gate charge characteristic

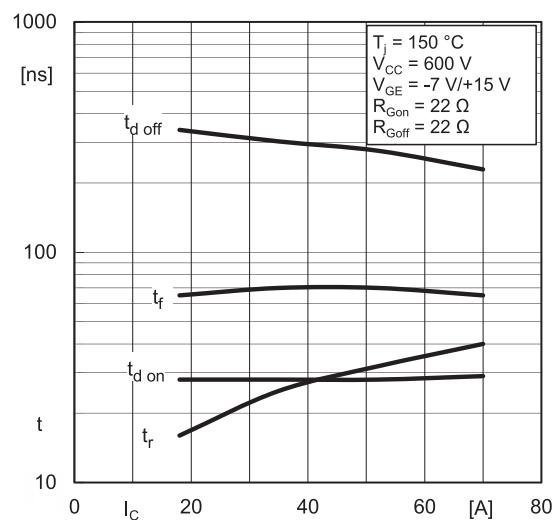


Fig. 7: Typ. switching times vs.  $I_C$

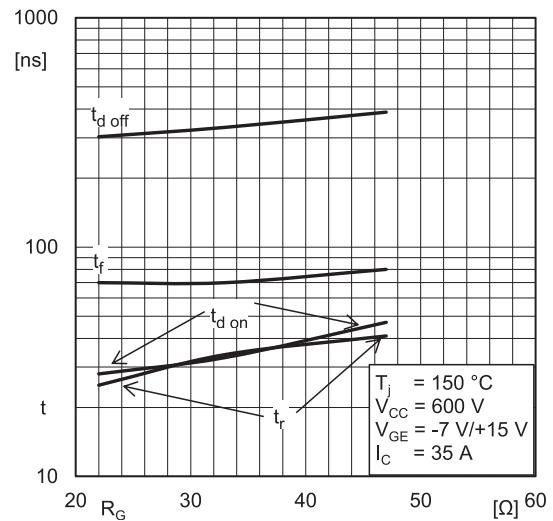


Fig. 8: Typ. switching times vs. gate resistor  $R_G$

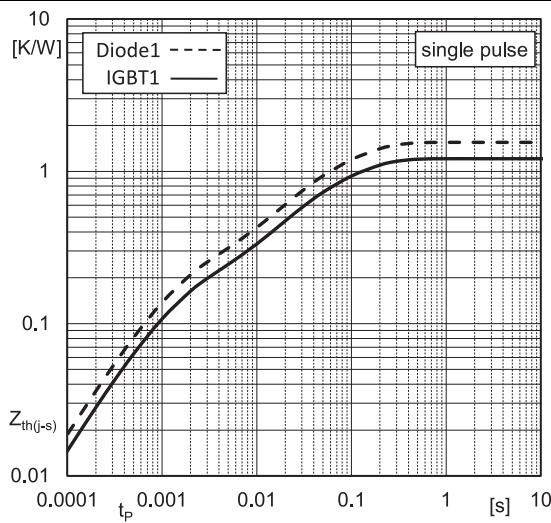


Fig. 9: Typ. transient thermal impedance

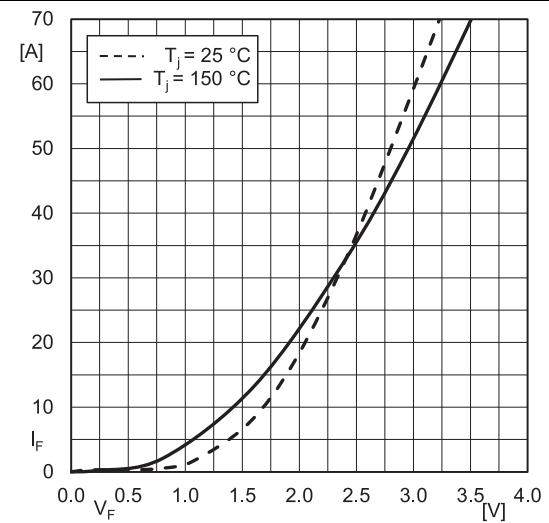
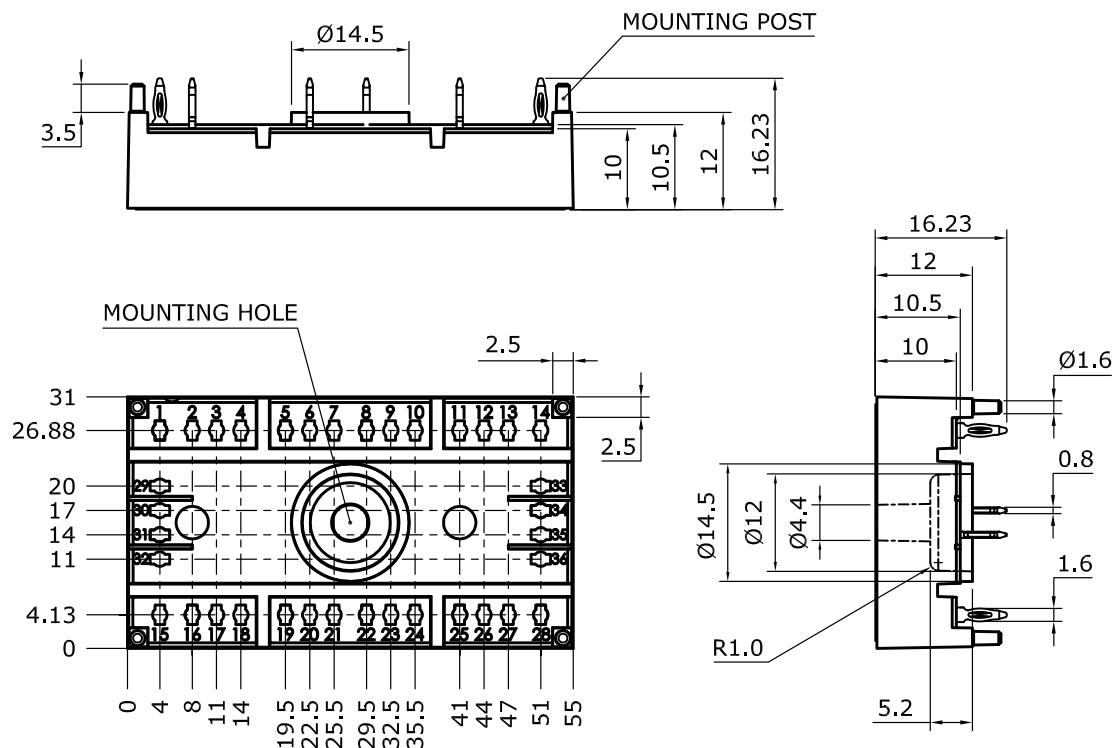


Fig. 10: Typ. CAL diode forward charact., incl.  $R_{CC} + EE'$

Dimensions: mm

## Tolerance system: ISO 2768-m



Suggested drilled hole diameter for terminal pins in the circuit board:

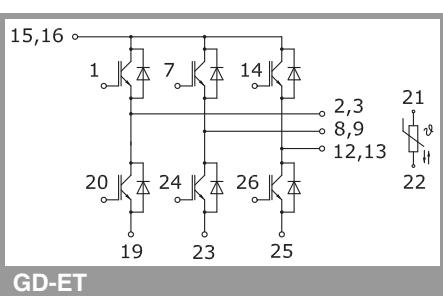
- minimum: 1.575 mm
- typical: 1.6 mm
- maximum: 1.625 mm

Suggested hole diameter for the mounting post in the circuit board:

- 2 mm

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SEMITOP 3 Press-Fit



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

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